



Shantou Huashan Electronic Devices Co.,Ltd.

HTF8A60

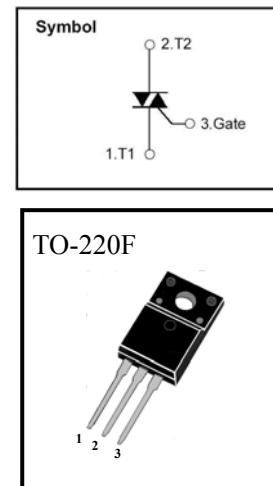
INSULATED TYPE TRIAC (TO-220F PACKAGE)

■ Features

- * Repetitive Peak Off-State Voltage: 600V
- * R.M.S On-state Current($I_{T(RMS)}=8A$)
- * High Commutation dv/dt

■ General Description

The Triac HTF8A60 is suitable for AC switching application, phase control application such as heater control, motor control, lighting control, and static switching relay.



■ Absolute Maximum Ratings ($T_a=25^\circ C$)

T_{stg}	Storage Temperature	-40~125°C
T_j	Operating Junction Temperature	-40~125°C
P_{GM}	Peak Gate Power Dissipation	5W
V_{DRM}	Repetitive Peak Off-State Voltage	600V
I_T (RMS)	R.M.S On-State Current ($T_a=89^\circ C$)	8A
V_{GM}	Peak Gate Voltage	10V
I_{GM}	Peak Gate Current	2.0A
I_{TSM}	Surge On-State Current (One Cycle, 50/60Hz,Peak,Non-Repetitive)	80/88A
V_{ISO}	Isolation Breakdown Voltage (RMS.A.C.1 minute)	1500V

■ Electrical Characteristics ($T_a=25^\circ C$)

Symbol	Items	Min.	Typ.	Max.	Unit	Conditions
I_{DRM}	Repetitive Peak Off-State Current			2.0	mA	$VD=VDRM$, Single Phase,Half Wave, $TJ=125^\circ C$
V_{TM}	Peak On-State Voltage			1.4	V	$I_T=12A$, Inst. Measurement
I^{+}_{GT1}	Gate Trigger Current (I)			30	mA	$V_D=6V$, $R_L=10$ ohm
I^{-}_{GT1}	Gate Trigger Current (II)			30	mA	$V_D=6V$, $R_L=10$ ohm
I^{-}_{GT3}	Gate Trigger Current (III)			30	mA	$V_D=6V$, $R_L=10$ ohm
V^{+}_{GT1}	Gate Trigger Voltage (I)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V^{-}_{GT1}	Gate Trigger Voltage (II)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V^{-}_{GT3}	Gate Trigger Voltage (III)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V_{GD}	Non-Trigger Gate Voltage	0.2			V	$T_j=125^\circ C$, $V_D=1/2V_{DRM}$
$(dv/dt)c$	Critical Rate of Rise of Off-State Voltage at Commutation	10			V/ μ S	$Tj=125^\circ C$, $VD=2/3VDRM$ $(di/dt)c=-4A/ms$
I_H	Holding Current		15		mA	
$R_{th(j-c)}$	Thermal Resistance			3.7	°C/W	Junction to case



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■ Performance Curves

Fig 1. Gate Characteristics

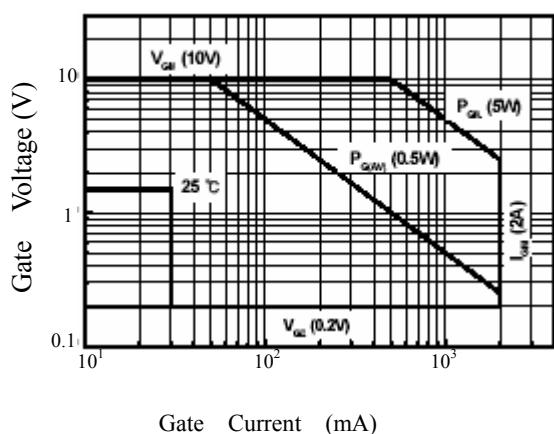


Fig 2. On-State Voltage

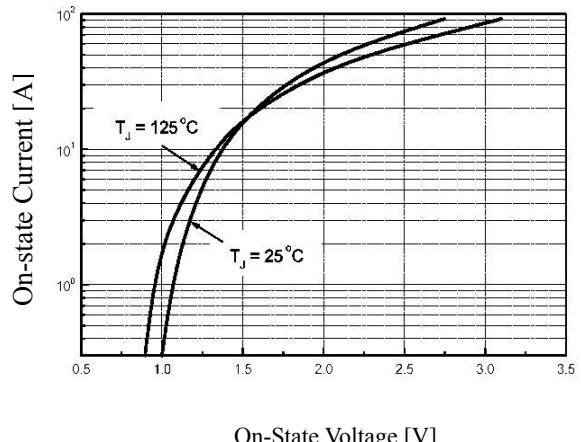


Fig 3. Gate Trigger Voltage vs. Junction Temperature

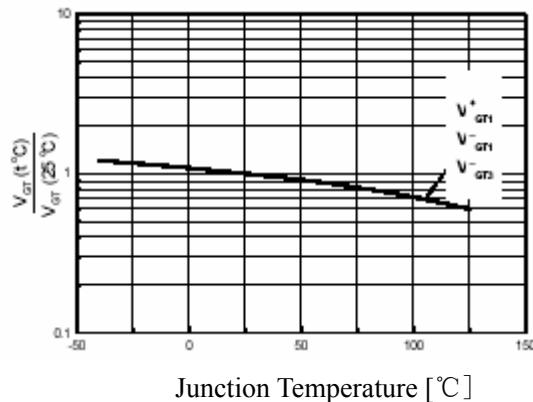


Fig 4. On State Current vs. Maximum Power Dissipation

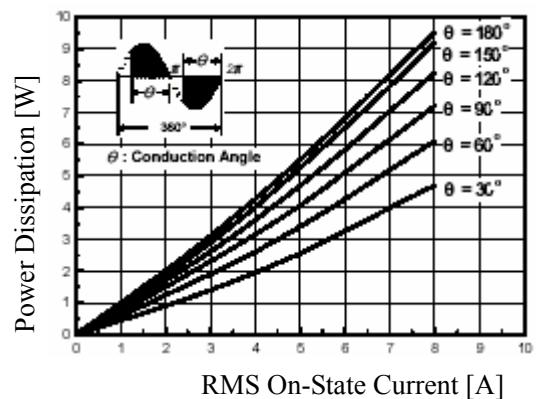


Fig 5. On State Current vs. Allowable Case Temperature

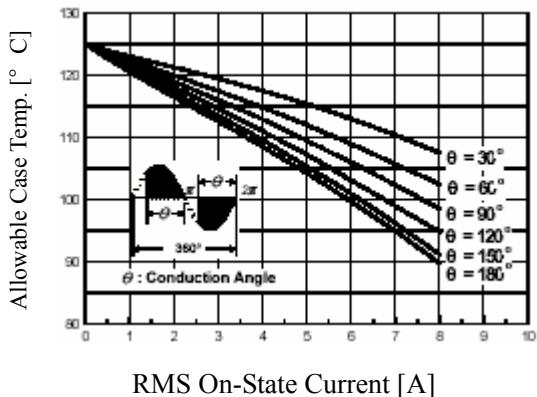
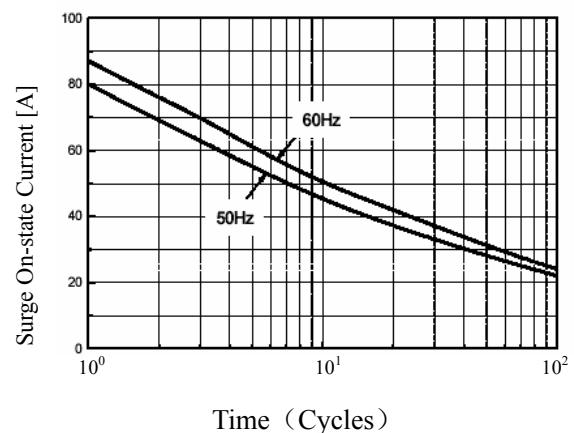


Fig 6. Surge On-State Current Rating (Non-Repetitive)





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Fig 7. Gate Trigger Current vs.
Junction Temperature

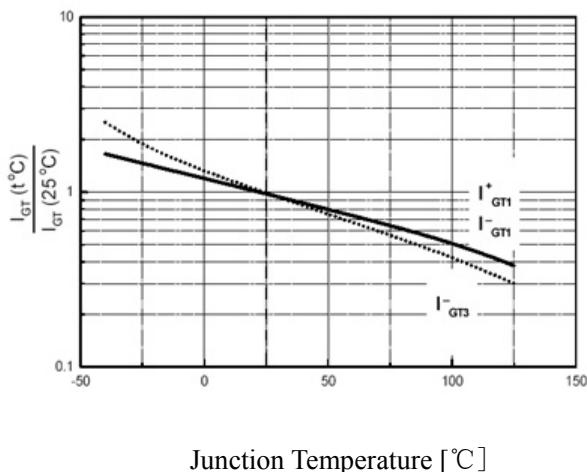


Fig 8. Transient Thermal Impedance

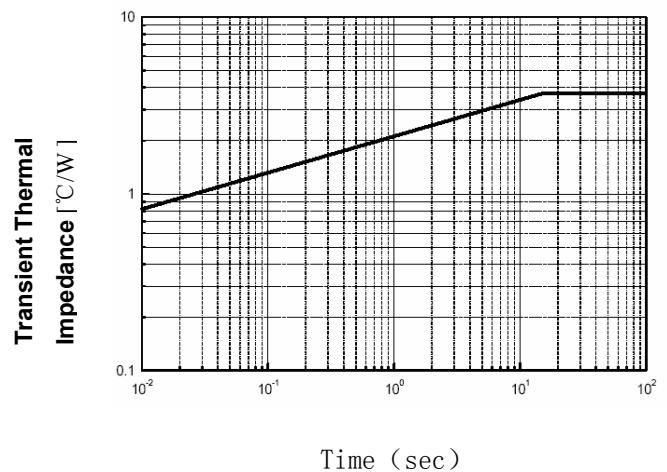
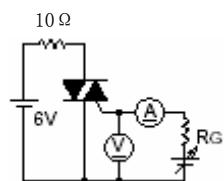
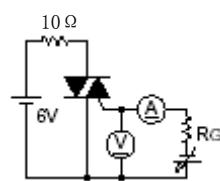


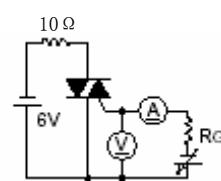
Fig 9. Gate Trigger Characteristics Test Circuit



Test Procedure I



Test Procedure II



Test Procedure III